

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A ceramic heater for heating a semiconductor wafer comprising:

a ceramic substrate, on a surface of which or inside which, a heating element pattern is formed,

wherein

said ceramic substrate comprises a ceramic sintered body containing at least one of Na, B, and Y as an impurity element.

said ceramic heater is constituted to have a structure such that a convex body or a convex portion is which can make a point contact with a semiconductor wafer is formed on the surface of said ceramic substrate so as to provide only one point of contact to the semiconductor wafer at the convex body or the convex portion, and

~~an object to be heated~~ the semiconductor wafer can be held apart from a surface of said ceramic substrate and heated.

Claim 2 (Currently Amended): A ceramic heater for heating a semiconductor wafer comprising:

a ceramic substrate, on a surface of which or inside which, a heating element pattern is formed,

wherein

said ceramic substrate comprises a ceramic sintered body containing at least one of Na, B, and Y as an impurity element,

said ceramic heater is constituted to have a structure such that a face of said ceramic substrate on which no heating element is formed or one face of said ceramic substrate is made to be a heating surface,

a convex body or a convex portion is which can make a point contact with a semiconductor wafer is formed on the surface of said ceramic substrate so as to provide only one point of contact to the semiconductor wafer at the convex body or the convex portion,
and

~~an object to be heated~~ a semiconductor wafer can be held apart from said heating surface and heated.

Claims 3-26 (Canceled)

Claim 27 (New): A ceramic heater for heating a semiconductor wafer comprising:

a ceramic substrate, on a surface of which or inside which, a heating element pattern is formed,

wherein

said ceramic substrate comprises a ceramic sintered body containing at least one of Na, B, and Y as an impurity element,

said ceramic heater is constituted to have a structure such that a convex body or a convex portion, which has at least one of a conical shape, a pyramidal shape, a spire shape, a spherical shape, and hemispherical shape, is formed on the surface of said ceramic substrate,
and

a semiconductor wafer can be held apart from a surface of said ceramic substrate and heated.

Claim 28 (New): A ceramic heater for heating a semiconductor wafer comprising:
a ceramic substrate, on a surface of which or inside which, a heating element pattern is formed,

wherein

said ceramic substrate comprises a ceramic sintered body containing at least one of Na, B, and Y as an impurity element,

said ceramic heater is constituted to have a structure that a face of said ceramic substrate on which no heating element is formed or one face of said ceramic substrate is made to be a heating surface,

a convex body or a convex portion, which has at least one of a conical shape, a pyramidal shape, a spire shape, spherical shape, and a hemispherical shape, is formed on the surface of said ceramic substrate, and

a semiconductor wafer can be held apart from said heating surface and heated.

Claim 29 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28, further comprising:

a through hole, in which a supporting pin configured to hold the semiconductor wafer is passed through, is formed in said ceramic substrate.

Claim 30 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein

said convex body or said convex portion is configured to hold the semiconductor wafer 5 to 5000 μm apart from the surface or the heating surface of said ceramic substrate.

Claim 31 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic substrate comprises at least one of nitride ceramics, carbide ceramics, and oxide ceramics.

Claim 32 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic substrate comprises a rare earth element oxide as a sintering aid.

Claim 33 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic substrate comprises 0.1 to 10% by weight of a sintering aid.

Claim 34 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic substrate comprises yttrium.

Claim 35 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic substrate comprises 200 to 5000 ppm of carbon.

Claim 36 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic heater is configured to be used at a temperature of 100°C or higher.

Claim 37 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said ceramic heater is configured to be used at a temperature of 200°C or higher.

Claim 38 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said heating element pattern comprises a metal foil or a metal wire.

Claim 39 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28,

wherein said heating element pattern comprises metal particles or a conductive ceramic.

Claim 40 (New): The ceramic heater for heating a semiconductor wafer according to any of Claims 1, 2, 27, and 28;

wherein said heating element pattern is a pattern of concentric circles.